

Communication

Polyhedral Oligomeric Silsesquioxane (POSS) Surface Grafting: A Novel Method to Enhance Polylactide Hydrolysis Resistance

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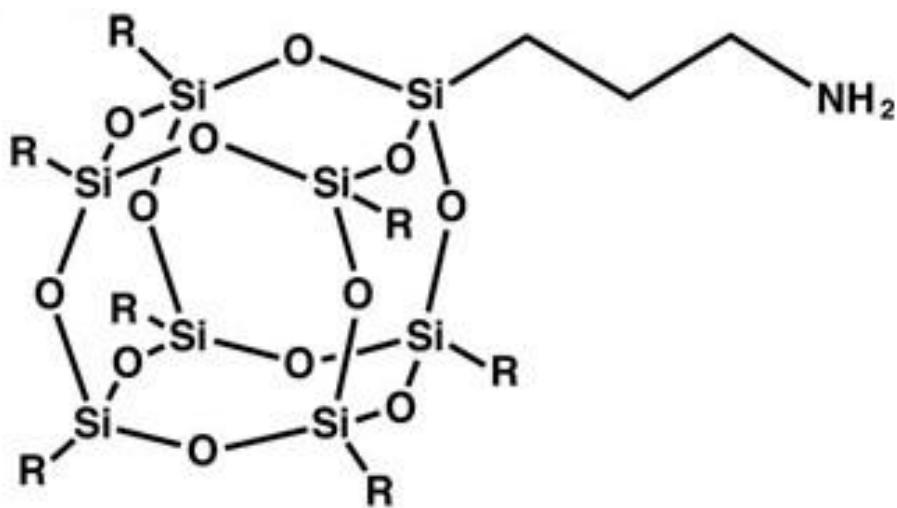


Figure S1. Aminopropyl heptaisobutyl POSS (POSS-NH₂).

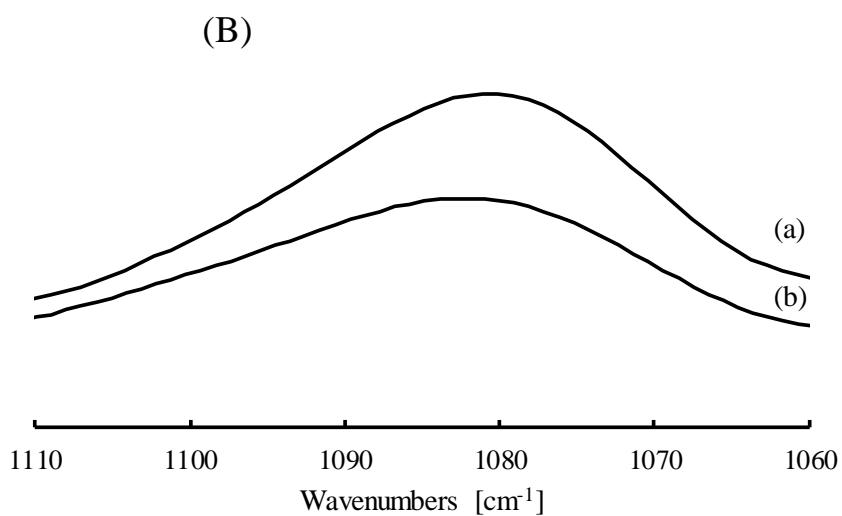
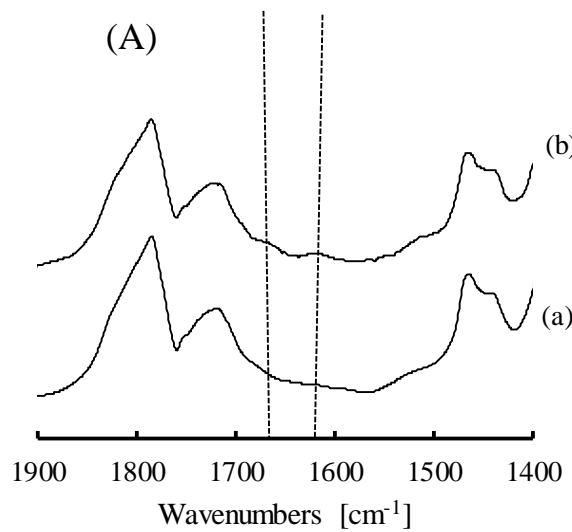


Figure S2. (A) FTIR spectra of: (a) PLLA neat film and (b) PLLA_{POSS_8_60} film in the range 1900–1400 cm⁻¹, (B) FTIR spectra of: (a) PLLA neat film and (b) PLLA_{POSS_8_60} film in the range 1110–1060 cm⁻¹.

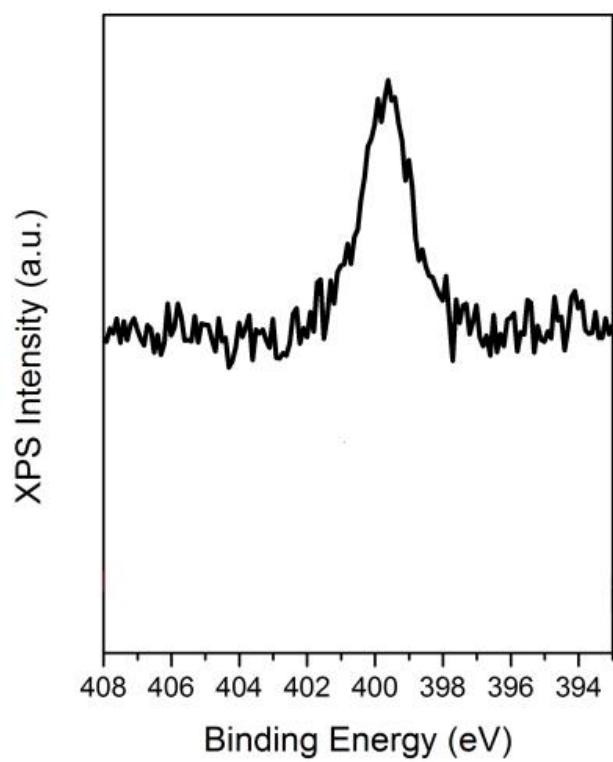


Figure S3. XPS spectrum collected on POSS-NH₂ powders. The data are shown in the energy region typical for N 1s photoelectrons after subtraction of Shirley-type background. Data are shown after normalization.

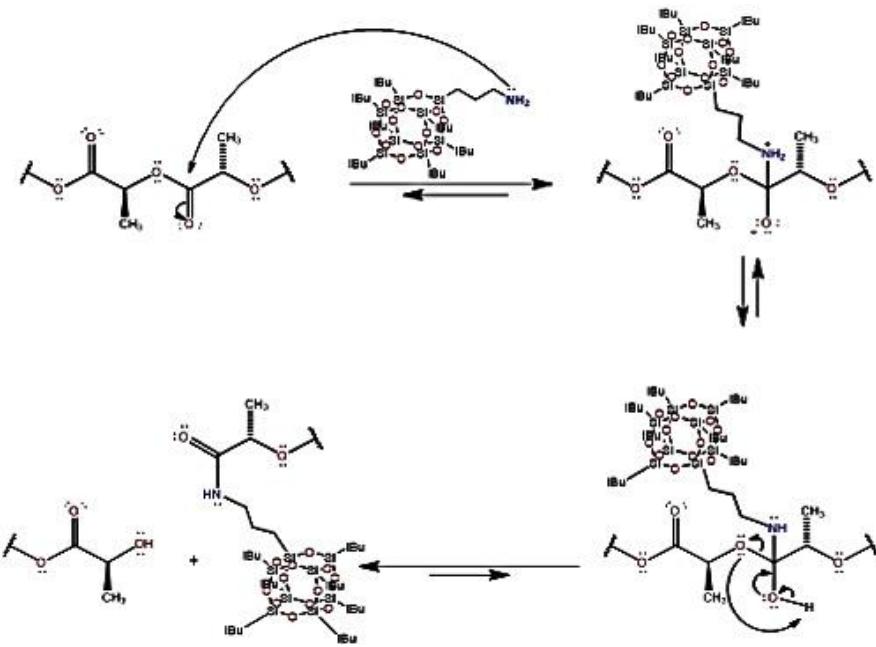


Figure S4. Reaction mechanism of the reaction between POSS-NH₂ and PLLA.

Table S1a. DSC results of neat PLLA and of treated films (second heating).

Sample code	T _g (°C)	T _{cc} (°C)	T _m (°C)	ΔH _{cc} (J/g)	ΔH _m (J/g)
PLLA	60	130	153	5	6
PLLA_POSS_4_40	61	133	154	5	6
PLA/POSS_8_40	60	131	154	4	6
PLLA_POSS_4_60	60	130	153	5	6
PLLA_POSS_8_60	348	130	153	5	6

T_g: glass transition temperature, T_{cc}: cold crystallization temperature, T_m: melting temperature, ΔH_{cc}: enthalpy of the cold crystallization, ΔH_m: melting enthalpy.

Table S1b Characterization results of neat PLLA and of treated films.

Sample code	T _{onset} (°C)	T _{max} (°C)	Contact angles (°)
PLLA	329	367	71 ± 2
PLLA_POSS_4_40	331	369	87 ± 1
PLA/POSS_8_40	334	371	91 ± 2
PLLA_POSS_4_60	341	374	91 ± 2
PLLA_POSS_8_60	348	378	101 ± 1

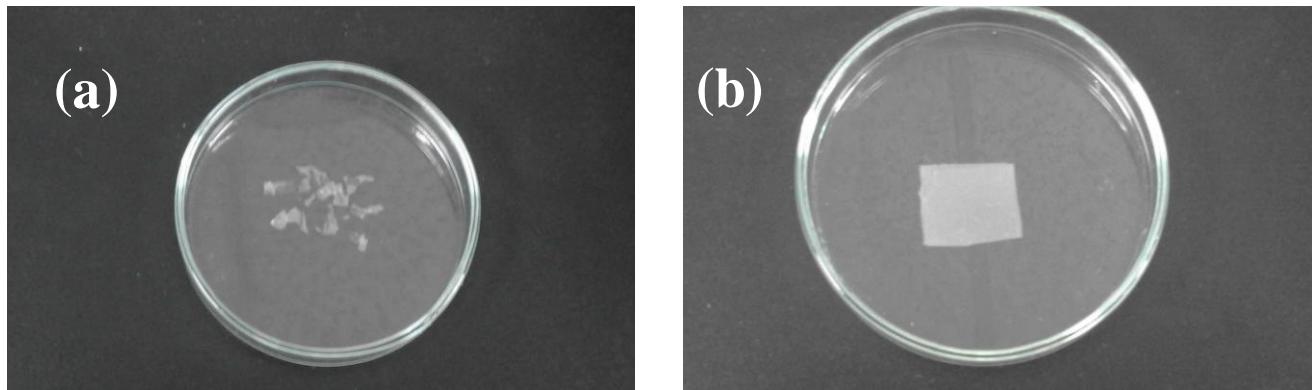


Figure S5. Photos of (a) PLLA film and (b) PLLA_P POSS_8_60 film after being in contact with the buffer for 4 weeks at 50 °C.